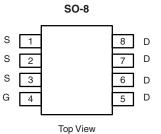


Vishay Siliconix

P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)			
- 40	0.014 at V _{GS} = - 10 V	- 10.5	40			
	0.021 at V _{GS} = - 4.5 V	- 8.7	40			



FEATURES

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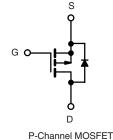
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC ٠



COMPLIANT

HALOGEN

FREE Available



Ordering Information: Si4401BDY-T1-E3 (Lead (Pb)-free) Si4401BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 40		V	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current /T 150 °C)	T _A = 25 °C	- I _D	- 10.5	- 8.7		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 8.3	- 5.9		
Pulsed Drain Current		I _{DM}	- 50		А	
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 2.6	- 1.36		
Avalanche Current		I _{AS}	30 45			
Single Pulse Avalanche Energy	L = 1 mH	E _{AS}			mJ	
	T _A = 25 °C	PD	2.9	1.5	W	
Maximum Power Dissipation ^a	T _A = 70 °C	'D	1.85	0.95	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 s	R _{thJA}	36	43	
Maximum Junction-to-Ambient ^a	Steady State		70	84	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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SPECIFICATIONS T ₁ = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
	I _{DSS}	V _{DS} = - 40 V, V _{GS} = 0 V		- 1			
Zero Gate Voltage Drain Current		V_{DS} = - 40 V, V_{GS} = 0 V, T_{J} = 70 °C			- 10	μA 10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -10 V$	- 30			А	
	R _{DS(on)}	$V_{GS} = -10 \text{ V}, I_D = -10.5 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -8.7 \text{ A}$		0.011	0.014	Ω	
Drain-Source On-State Resistance ^a				0.0165	0.021		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 10.5 A		26		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 2.7 A, V _{GS} = 0 V		- 0.74	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Qg			40	55		
Gate-Source Charge	Q _{gs}	V_{DS} = - 15 V, V_{GS} = - 5 V, I_{D} = - 10.5 A		10		nC	
Gate-Drain Charge	Q _{gd}			14			
Gate Resistance	Rg		1.4	2.8	4.2	Ω	
Turn-On Delay Time	t _{d(on)}			16	25		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		15	25		
Turn-Off Delay Time	t _{d(off)}	${\rm I}_{\rm D}\cong$ - 1 A, ${\rm V}_{\rm GEN}$ = - 10 V, ${\rm R}_{\rm g}$ = 6 Ω		97	150	ns	
Fall Time	t _f			47	75		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dl/dt = 100 A/μs		35	55		

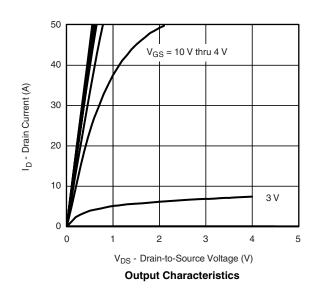
Notes:

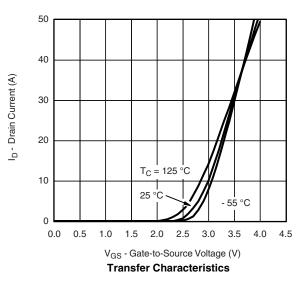
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



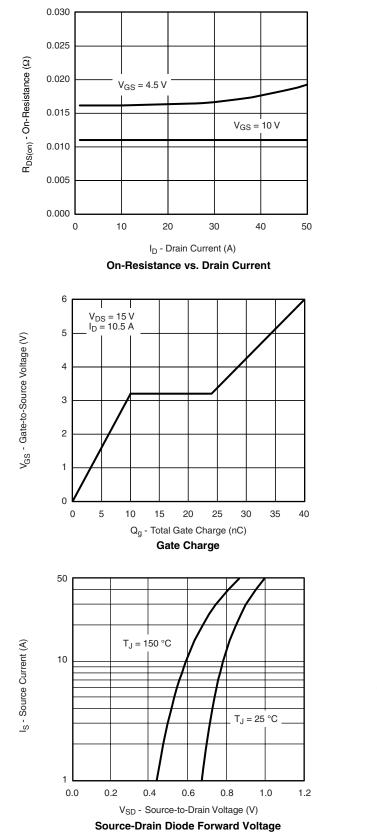


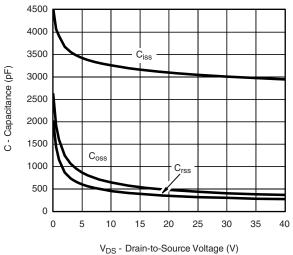


Si4401BDY

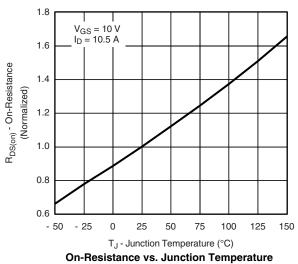
Vishay Siliconix

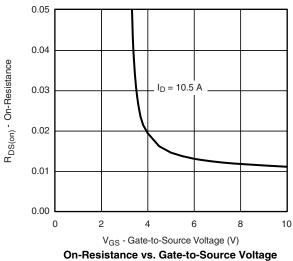
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted











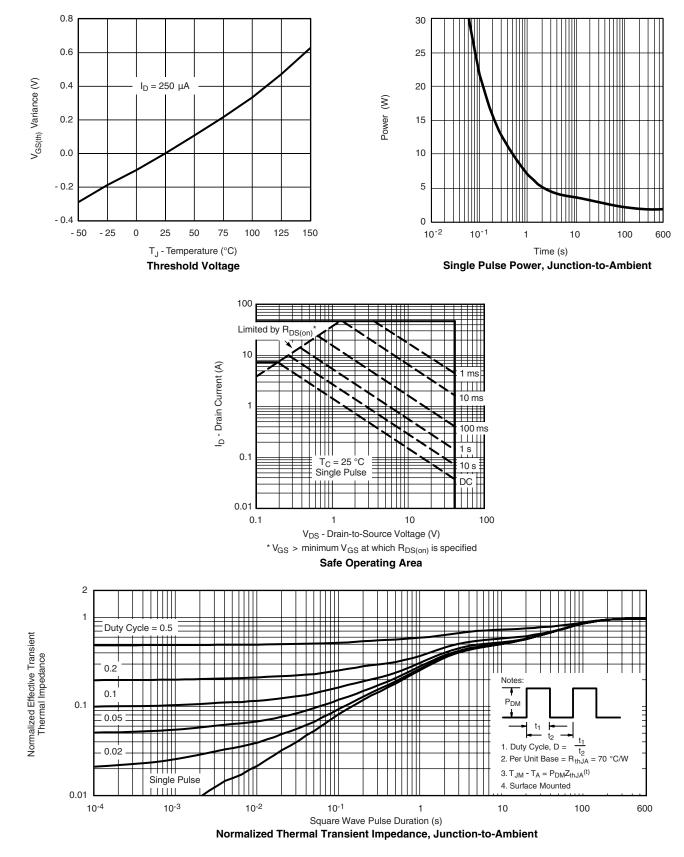
Document Number: 73140 S09-0866-Rev. D, 18-May-09

Si4401BDY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

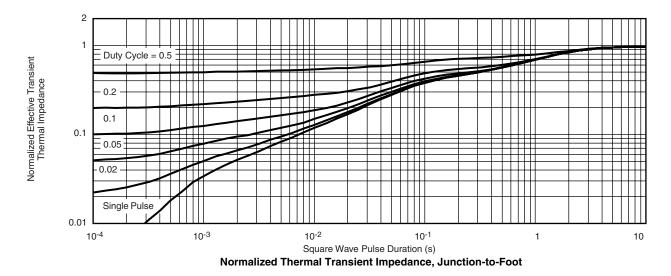




Si4401BDY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg773140.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INCHES			
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050	50 BSC		
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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